

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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TSC5302D

High Voltage NPN Transistor with Diode



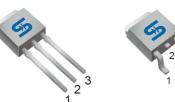
TO-251

(IPAK)

TO-252 (DPAK)



Collector
 Emitter



PRODUCT SUMMARY

BV _{CEO}	400V
BV _{CBO}	700V
Ic	2A
V _{CE(SAT)}	1.1V @ I _C =1A, I _B =0.25A

Features

- Build-in Free-wheeling Diode Makes Efficient Anti-saturation Operation
- No Need to Interest h_{FE} Value Because of Low Variable Storage-time Spread Even Though Comer Spirit Product.
- Low Base Drive Requirement
- Suitable for Half Bridge Light Ballast Application

Structure

- Silicon Triple Diffused Type
- NPN Silicon Transistor with Diode

Ordering Information

Part No.	Package	Packing
TSC5302DCP ROG	TO-252	2.5kpcs / 13" Reel
TSC5302DCH C5G	TO-251	75pcs / Tube

Note: "G" denote for Halogen Free Product

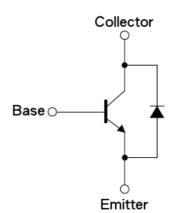
Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		V _{CBO}	700	V	
Collector-Emitter Voltage		V_{CEO}	400	V	
Emitter-Base Voltage		V_{EBO}	10	V	
Collector Current		I _C	2	Α	
Collector Peak Current (tp <5ms)		I _{CM}	4	Α	
Base Current		I _B	1	Α	
Base Peak Current (tp <5ms)		I _{BM}	2	Α	
Total Dissipation @ Tc ≤ 25°C	TO-251	Б	1.5	W	
	TO-252	P _{tot}	25		
Maximum Operating Junction Temperature		TJ	+150	°C	
Storage Temperature Range		T _{STG}	-65 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\Theta_{JC}$	6.25	°C/W
Junction to Ambient Thermal Resistance	RO _{JA}	100	°C/W

Block Diagram





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Pb RoHS

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Base Voltage	$I_{C} = 1 \text{mA}, I_{B} = 0$	BV _{CBO}	700			V
Collector-Emitter Breakdown Voltage ^a	$I_{C} = 10 \text{mA}, I_{E} = 0$	BV _{CEO}	400			V
Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	BV_{EBO}	10			V
Collector Cutoff Current	$V_{CB} = 700V, I_{E} = 0$	I _{CBO}	1		1	μΑ
Emitter Cutoff Current	$V_{EB} = 9V, I_{C} = 0$	I _{EBO}	-		1	μΑ
Collector-Emitter Saturation Voltage ^a	I _C =0.5A, I _B =0.1A	V _{CE(SAT)1}	-		0.5	.,
	I _C =1A, I _B =0.25A	V _{CE(SAT)2}	-	1.1	1.5	V
Base-Emitter Saturation Voltage ^a	I _C =0.5A, I _B =0.1A	V _{BE(SAT)1}	I		1.1	V
	I _C =1A, I _B =0.25A	V _{BE(SAT)2}			1.2	
DC Current Gain	V_{CE} =5V, I_{C} =10mA	h _{FE} 1	10			
	V _{CE} =5V, I _C =400mA	h _{FE} 2	10		30	
	V _{CE} =5V, I _C =1A	h _{FE} 3	5			
Turn On Time	$V_{CC} = 250V, I_{C} = 1A,$	t _{ON}		0.15	0.3	μs
Storage Time	$I_{B1}=I_{B2}=0.2A$, $t_p=25\mu s$	t _{STG}		0.5	0.9	μs
Fall Time	Duty Cycle<1%	t _f		0.2	0.4	μs
Diode						
Fall Time	I _C =1A	t _F	-		800	μs
Forward Voltage Drop	I _C =1A	Vf			1.4	V

Notes: Pulsed duration = 300µs, duty cycle ≤2%



Ph RoHS

High Voltage NPN Transistor with Diode

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

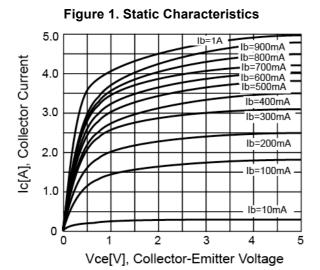


Figure 3. Vce(sat) vs. Vbe(sat)

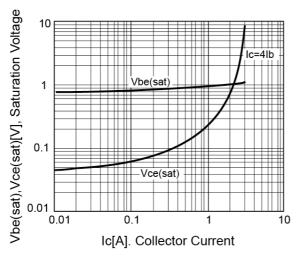


Figure 5. Reverse Bias SOA

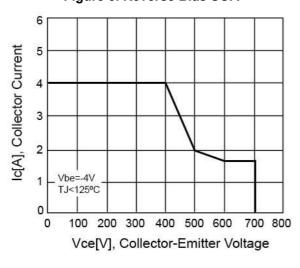


Figure 2. DC Current Gain

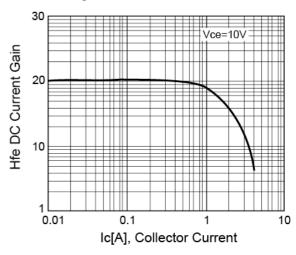


Figure 4. Power Derating

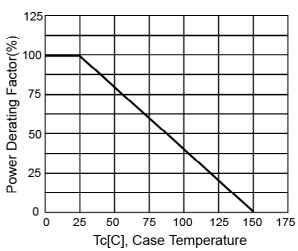
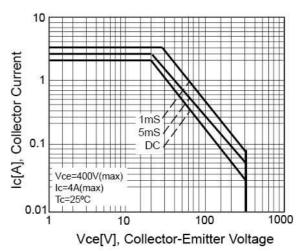


Figure 6. Safe Operating Area

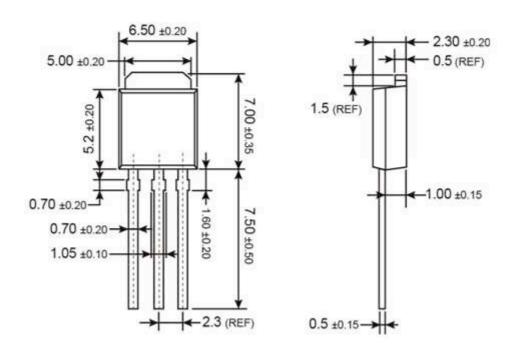






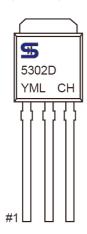
High Voltage NPN Transistor with Diode

TO-251 Mechanical Drawing



Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product
 (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep,
 X=Oct, Y=Nov, Z=Dec)

L = Lot Code

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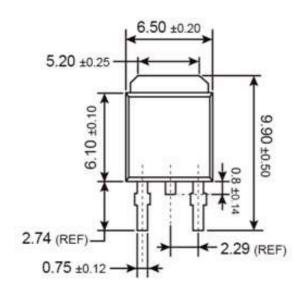
Version: G14

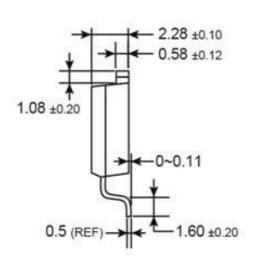




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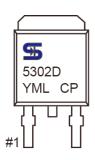
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